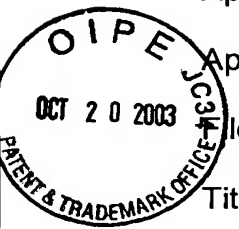


IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Applicant : YEH
Application No. : 10/601,701
Filed : June 24, 2003
Title : METHOD FOR FABRICATION OF POLYCRYSTALLIN SILICON THIN FILM TRANSISTORS
Group Art Unit : 2812
Examiner : Unknown
Docket No. : BHT/3230-56

MAIL STOP
OFFICE OF INITIAL PATENT EXAMINATION
Honorable Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

TRANSMITTAL COVER SHEET

Sir:

Transmitted herewith for filing are the following:

1. INFORMATION DISCLOSURE STATEMENT.
2. Form PTO-1449 (in duplicate), along with copies of nine (9) references cited therein.

The Commissioner is hereby authorized to charge any fees which may be required for the filing of this document to **Deposit Account No. 501874**.

Respectfully submitted,

Date: October 20, 2003

By:


Bruce H. Troxell
Reg. No. 26,592

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INFORMATION DISCLOSURE STATEMENT

Sir:

In compliance with the duty of disclosure under 37 CFR 1.56, and 37 CFR 1.97-1.98, the documents listed on the attached form PTO-1449 are hereby made of record in this patent application. Copies of the listed documents are enclosed.

As this Information Disclosure Statement is being filed prior to the mailing of the first Official Action in this application, no fee is believed due in order to have the enclosed references considered by the Examiner and made of record in the application.

Early action on the merits of the application is earnestly solicited.

Respectfully submitted,

Date: October 20, 2003

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FORM PTO 1449 (modified)

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICELIST OF REFERENCES CITED BY APPLICANT(S)
(Use several sheets if necessary)Date Submitted to PTO: **October 20, 2003**ATTY DOCKET NO. **BHT/3230-56**APPLICATION NO. **10/601,701**APPLICANT **YEH**FILING DATE **Jun 24, 2003**GROUP **2812**

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
OCT 20 2003	4,330,363	05/18/82	Biegesen et al.			
	4,592,799	06/03/86	Hayafuji			
	5,021,119	06/04/91	Fan et al.			
	5,395,481	03/07/95	McCarthy			
	6,495,405 B2	12/17/02	Voutsas et al.			

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)

	High-Performance Low-Temperature Poly-Si TFTs Crystallized by Excimer Laser with Recessed-Channel Structure, Lin et al., IEEE Electron Device Letters, Vol. 22, No. 6, June 2001, pages 269-271
	Performance Improvement Obtained for Thin-Fil Transistors Fabricated in Prepatterned Laser-Recrystallized Polysilicon, Giust et al., IEEE Electron Device Letters, Vol. 18, No. 6, June 1997, pages 296-298
	Comparison of excimer laser recrystallized prepatterned and unpatterned silicon films on SiO₂, Giust et al., J.Appl.Phys. 81(3), 1 February 1997, pages 1204-1211
	High-Performance Single Crystalline-Silicon TFTs on a Non-Alkali Glass Substrate, Sano et al. Fujitsu Laboratories Ltd., Atsugi 243-0197, Japan (C) 2002 IEEE

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.